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## **SB3100 SCHOTTKY RECTIFIER**

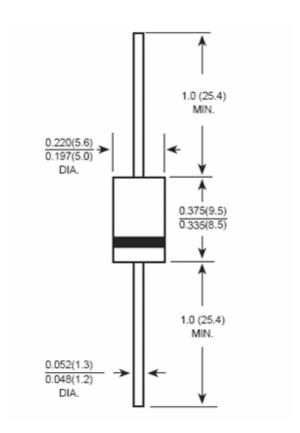
## **Applications:**

- Disk Drives
- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection
- Battery Charging

#### Features:

- Small foot print, surface moutable
- Low forward voltage drop
- High frequency operation
- . Guard ring for enhanced ruggedness and long term reliability
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

#### Mechanical Dimensions: In Inches / mm



**DO-201AD** 



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## **Marking Diagram:**



## Where XXXXX is YYWWL

SB = Device Type
3 = Forward Current (3A)
100 = Reverse Voltage (100V)
SSG = SSG
YY = Year
WW = Week
L = Lot Number

Cautions: Molding resin

Epoxy resin UL:94V-0

## **Ordering Information:**

Device	Package	Shipping
SB3100	DO-201AD (Pb-Free)	1250pcs / tape

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification.

## **Maximum Ratings:**

Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	$V_{RWM}$	-	100	V
Max. Average Forward	I <sub>F(AV)</sub>	50% duty cycle @TC =105°C rectangular wave form(L=0.375")	3.0	А
Max. Peak One Cycle Non-Repetitive Surge Current	I <sub>FSM</sub>	8.3 ms, half Sine pulse	110	A

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## **Electrical Characteristics:**

Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage Drop	$V_{F1}$	@ 3A, Pulse, T <sub>J</sub> = 25°C	0.79	V
Max. Reverse Current	I <sub>R1</sub>	$@V_R = \text{rated VR}$ $T_J = 25^{\circ}C$	1.0	mA
	I <sub>R2</sub>	$@V_R = \text{rated VR}$ $T_J = 100^{\circ}C$	10	mA
Typical Junction Capacitance	Cj	$@V_R = 5.0 \text{ V, Tc=}25^{\circ}\text{C}$ $f_{SIG} = 1\text{MHz}$	250	pF

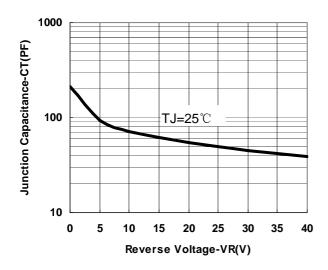
Pulse Width < 300µs, Duty Cycle <2%

# **Thermal-Mechanical Specifications:**

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature Range	T <sub>J</sub>	-	-55 to +150	$^{\circ}\mathbb{C}$
Storage Temperature Range	T <sub>stg</sub>	-	-55 to +150	$^{\circ}\mathbb{C}$
Maximum Thermal	$R_{\theta JC}$	DC operation	8	°C/W
Resistance Junction to Case				
Approximate Weight	wt	-	1.02	g
Case Style		DO-201AD		

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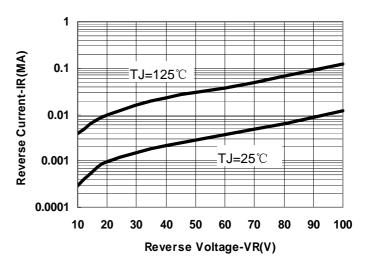


Fig.1-Typical Junction Capacitance Vs.Reverse Voltage

Fig.2-Typical Values Of Reverse Current Vs.Reverse Voltage

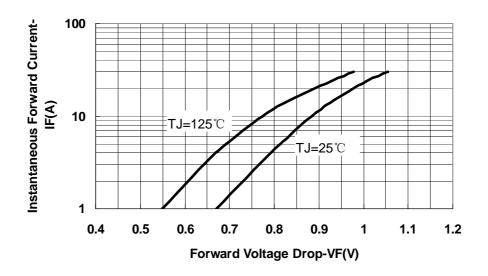


Fig.3-Typical Forward Voltage Drop Characteristics

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